

SD49xx: 50 V RF MOSFETs for ISM applications



STMicroelectronics

New DMOS series for ISM applications provides better RF performance, higher ruggedness and improved reliability

The new SD49xx series is designed especially for industrial scientific and medical applications. It uses an optimized process layout in order to improve RF performances over HF and VHF frequency bands.

It exhibits outstanding RF gain and power saturation, higher breakdown voltage, improved ruggedness and reliability (higher MTTF), resulting in a high-performance and cost-effective solution.

Key features

- $V_{(BR)DSS} > 200\text{ V}$
- Operating voltage up to 80 V
- $P_{OUT} > 300\text{ W @ } 50\text{ V}$
- Gain $> 20\text{ dB}$ at 30 MHz
- Efficiency $> 60\%$
- 20:1 all phases - load mismatch capability

Key benefits

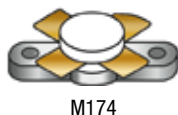
- Enhanced gain and P_{SAT}
- Excellent thermal behavior
- High ruggedness
- Greater reliability
- Higher breakdown voltage versus competition

Targeted applications

- Plasma enhanced CVD
- Plasma sputtering
- CO_2 laser drivers
- HF transceivers

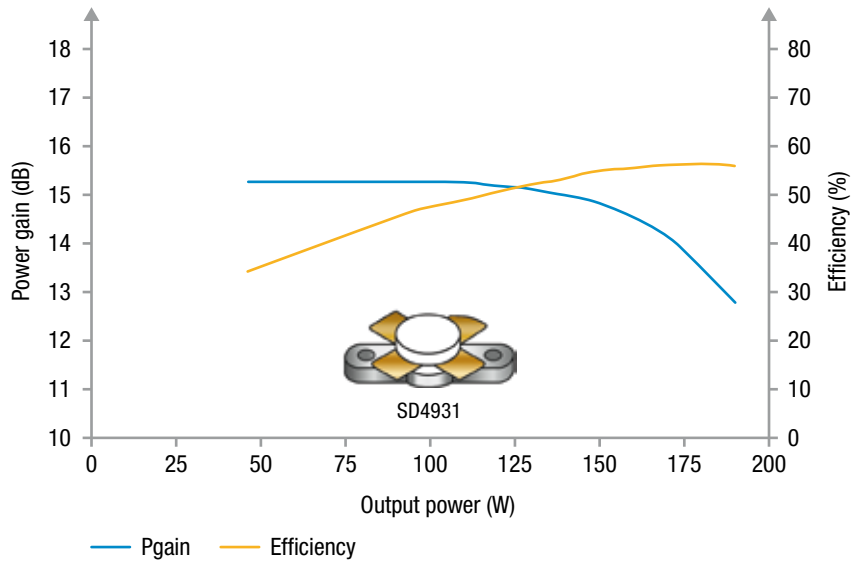


M177

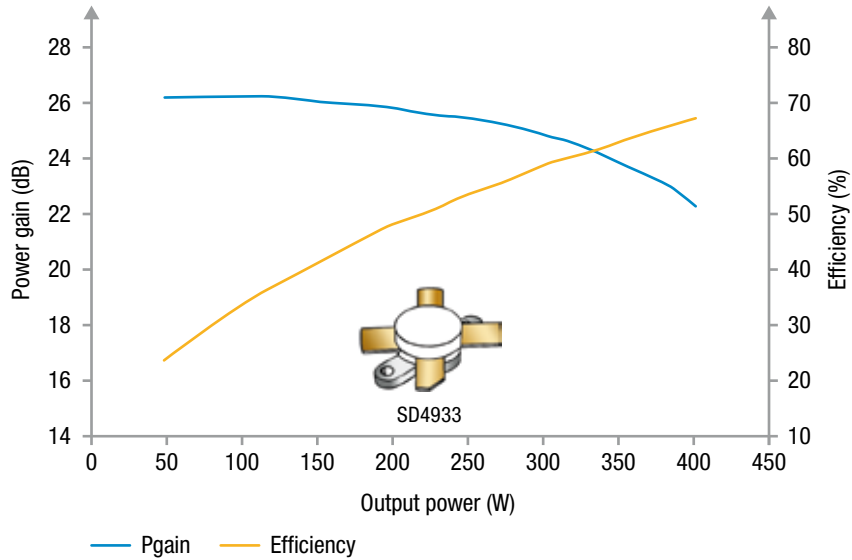


M174

Power gain and efficiency vs output power
 $V_{dd} = 50\text{ V}$, $I_{dq} = 250\text{ mA}$, Freq = 175 MHz



Power gain and efficiency vs output power
 $V_{dd} = 50\text{ V}$, $I_{dq} = 250\text{ mA}$, Freq = 30 MHz



Product table

Part number	Package	Frequency nom. (MHz)	Output power (Pout) nom. (W)	Power gain (PG) nom. (dB)	Transistor supply voltage (Vdd or Vcc) nom. (V)	Efficiency nom. (%)
SD4931	M174	175	150	14.8	50	56
SD4933	M177	30	300	24	50	65

